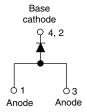


Vishay Semiconductors

Schottky Rectifier, 10 A





D-PAK (TO-252AA)

PRODUCT SUMMARY							
Package	D-PAK (TO-252AA)						
I _{F(AV)}	10 A						
V_{R}	45 V						
V _F at I _F	0.57 V						
I _{RM}	15 mA at 125 °C						
T _J max.	175 °C						
Diode variation	Single die						
E _{AS}	20 mJ						

FEATURES

- Popular D-PAK outline
- Small foot print, surface mountable



- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Compliant to RoHS Directive 2002/95/EC
- \bullet Meets MSL level 1, per J-STD-020, LF maximum peak of 260 $^{\circ}\text{C}$

DESCRIPTION

The VS-STPS1045BPbF surface mount Schottky rectifier has been designed for applications requiring low forward drop and small foot prints on PC board. Typical applications are in disk drives, switching power supplies, converters, freewheeling diodes, battery charging, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS									
SYMBOL	CHARACTERISTICS	VALUES	UNITS						
I _{F(AV)}	Rectangular waveform	10	А						
V _{RRM}		45	V						
I _{FSM}	t _p = 5 μs sine	390	А						
V _F	10 Apk, T _J = 125 °C	0.57	V						
TJ	Range	- 40 to 175	°C						

VOLTAGE RATINGS								
PARAMETER	SYMBOL	VS-STPS1045BPbF	UNITS					
Maximum DC reverse voltage	V_{R}	45	V					
Maximum working peak reverse voltage	V_{RWM}	43	V					

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST COND	TEST CONDITIONS					
Maximum average forward current See fig. 5	I _{F(AV)}	50 % duty cycle at T _C = 151 °C	10					
Maximum peak one cycle non-repetitive surge current	1	5 µs sine or 3 µs rect. pulse	Following any rated load condition and with rated	390	Α			
See fig. 7	IFSM	10 ms sine or 6 ms rect. pulse						
Non-repetitive avalanche energy	E _{AS}	$T_J = 25 ^{\circ}\text{C}, I_{AS} = 3.0 \text{A}, L = 4.40 \text{C}$	20	mJ				
Repetitive avalanche current	I _{AR}	Current decaying linearly to zer Frequency limited by T_J maxim	3.0	Α				

VS-STPS1045BPbF

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ELECTRICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST COND	VALUES	UNITS					
		10 A	T _{.1} = 25 °C	0.63					
Maximum forward voltage drop	V (1)	20 A	11 = 23 0	0.84	V				
See fig. 1	V _{FM} ⁽¹⁾	10 A	T _{.1} = 125 °C	0.57					
		20 A	1j = 125 C	0.72					
Maximum reverse leakage current	I _{RM} ⁽¹⁾	T _J = 25 °C	V _B = Rated V _B	0.2	mΛ				
See fig. 2		T _J = 125 °C	V _R = nateu V _R	15	- mA				
Typical junction capacitance	C _T	V _R = 5 V _{DC} (test signal range	760	pF					
Typical series inductance	L _S	Measured lead to lead 5 mm	5.0	nΗ					
Maximum voltage rate of change	dV/dt	Rated V _R	10 000	V/µs					

Note

 $^{^{(1)}\,}$ Pulse width < 300 µs, duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range	T _J ⁽¹⁾ , T _{Stg}		- 40 to 175	°C				
Maximum thermal resistance, junction to case	R _{thJC}	DC operation See fig. 4	3.0	°C/W				
Maximum thermal resistance, junction to ambient	R _{thJA}		50	C/VV				
Approximate weight			0.3	g				
Approximate weight			0.01	oz.				
Marking device		Case style D-PAK (similar to TO-252AA)	STPS1	1045B				

Note

(1) $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{thJA}}$ thermal runaway condition for a diode on its own heatsink



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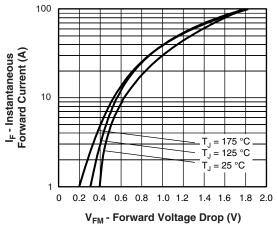


Fig. 1 - Maximum Forward Voltage Drop Characteristics

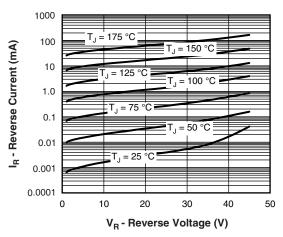


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

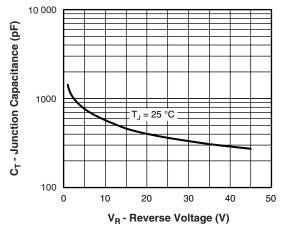


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

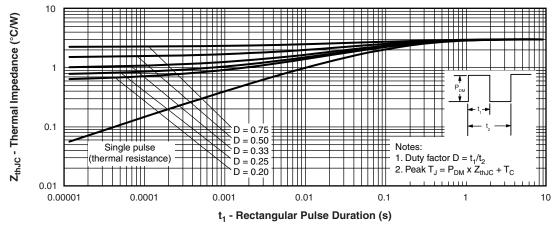


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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Schottky Rectifier, 10 A



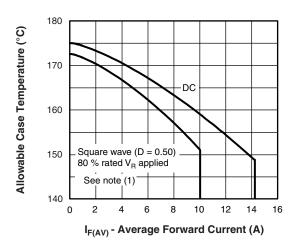


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

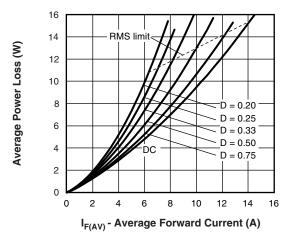


Fig. 6 - Forward Power Loss Characteristics

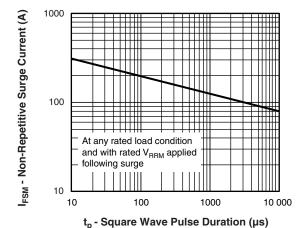


Fig. 7 - Maximum Non-Repetitive Surge Current

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}$; $Pd = Forward power loss = I_{F(AV)} \times V_{FM} at (I_{F(AV)}/D)$ (see fig. 6); $Pd_{REV} = Inverse power loss = V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = 80 \%$ rated V_R

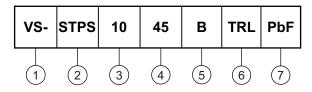


Schottky Rectifier, 10 A

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Schottky STPS series
- Current rating (10 A)
 - Voltage rating (45 = 45 V)
 - B = Essential part number
- • None = Tube (50 pieces)
 - TR = Tape and reel
 - TRL = Tape and reel (left oriented)
 - TRR = Tape and reel (right oriented)
- 7 PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95016						
Part marking information	www.vishay.com/doc?95059						
Packaging information	www.vishay.com/doc?95033						



Vishay Semiconductors

NOTES

3

2

MAX.

0.410

0.070

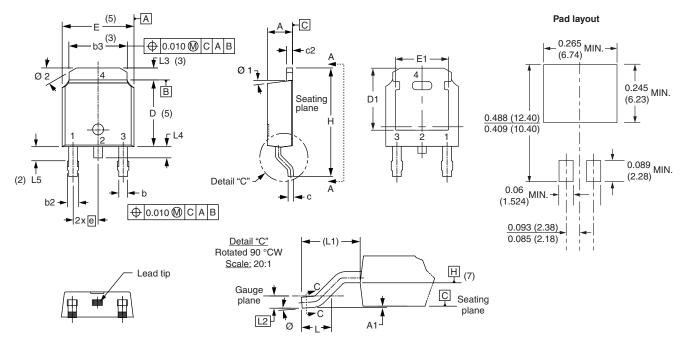
0.050

0.040

0.060

D-PAK (TO-252AA)

DIMENSIONS in millimeters and inches



Ī	SYMBOL	MILLIMETERS	INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES			
	STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIBUL	MIN.	MAX.	MIN.	MAX
ſ	Α	2.18	2.39	0.086	0.094			е	2.29	BSC	0.090	BSC
ſ	A1	-	0.13		0.005			Н	9.40	10.41	0.370	0.41
Ī	b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.07
Ī	b2	0.76	1.14	0.030	0.045			L1	2.74	BSC	0.108	REF.
ſ	b3	4.95	5.46	0.195	0.215	3		L2	0.51	BSC	0.020	BSC
Ī	С	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.05
Ī	c2	0.46	0.89	0.018	0.035			L4	-	1.02	-	0.04
ſ	D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.06
Ī	D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°
ſ	Е	6.35	6.73	0.250	0.265	5		Ø1	0°	15°	0°	15°
Ī	E1	4.32	-	0.170	-	3		Ø2	25°	35°	25°	35°

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- Lead dimension uncontrolled in L5
- Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- Dimension b1 and c1 applied to base metal only
- (7) Datum A and B to be determined at datum plane H
- Outline conforms to JEDEC outline TO-252AA



Legal Disclaimer Notice

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